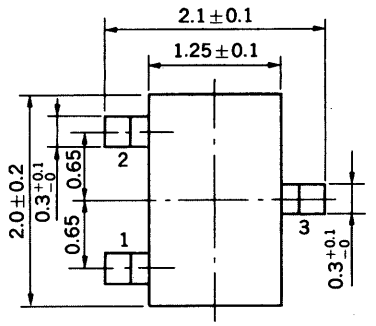
DATA SHEET

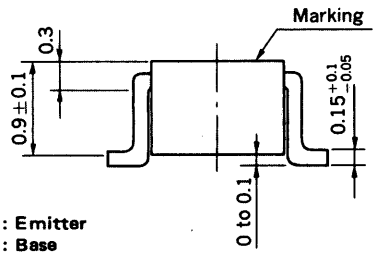
NEC
ELECTRON DEVICE

# SILICON TRANSISTOR
# GN1L3M

## MEDIUM SPEED SWITCHING
## RESISTOR BUILT-IN TYPE PNP TRANSISTOR

**PACKAGE DIMENSIONS**
in millimeters



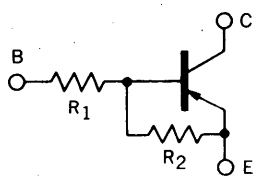




1 : Emitter
2 : Base
3 : Collector

Marking: M81

### FEATURES

- Resistors Built-in TYPE




$R_1$ = 4.7 kΩ
$R_2$ = 4.7 kΩ

- Complementary to GA1L3M

### ABSOLUTE MAXIMUM RATINGS

| | | | |
|---|---|---|---|
| Maximum Voltages and Currents ($T_a$ = 25 °C) | | | |
| Collector to Base Voltage | $V_{CBO}$ | −60 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | −50 | V |
| Emitter to Base Voltage | $V_{EBO}$ | −10 | V |
| Collector Current (DC) | $I_C$ | −100 | mA |
| Collector Current (Pulse) | $I_C$ | −200 | mA |
| Maximum Power Dissipation | | | |
| Total Power Dissipation at 25 °C Ambient Temperature | $P_T$ | 150 | mW |
| Maximum Temperatures | | | |
| Junction Temperature | $T_j$ | 150 | °C |
| Storage Temperature Range | $T_{stg}$ | −55 to +150 | °C |

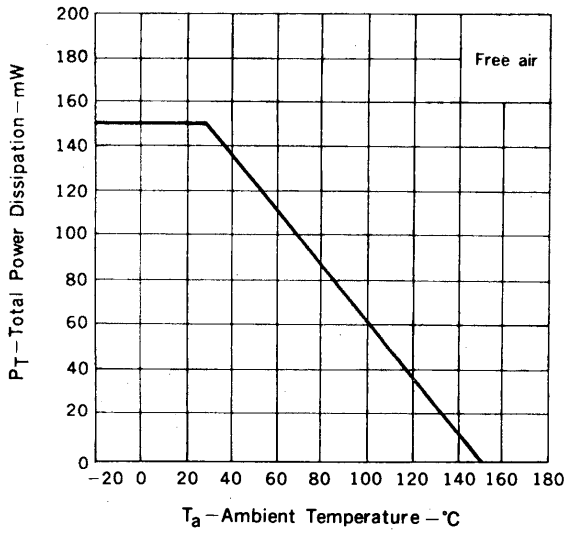
### ELECTRICAL CHARACTERISTICS ($T_a$ = 25 °C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|---|---|---|---|---|---|---|
| Collector Cutoff Current | $I_{CBO}$ | | | −100 | nA | $V_{CB}$ = −50 V, $I_E$ = 0 |
| DC Current Gain | $h_{FE1}$* | 20 | 40 | 80 | | $V_{CE}$ = −5.0 V, $I_C$ = −5.0 mA |
| DC Current Gain | $h_{FE2}$* | 70 | 110 | | | $V_{CE}$ = −5.0 V, $I_C$ = −50 mA |
| Collector Saturation Voltage | $V_{CE(sat)}$* | | −0.08 | −0.3 | V | $I_C$ = −5.0 mA, $I_B$ = −0.25 mA |
| Low-Level Input Voltage | $V_{IL}$* | | −1.1 | −0.8 | V | $V_{CE}$ = −5.0 V, $I_C$ = −100 μA |
| High-Level Input Voltage | $V_{IH}$* | −3.0 | −1.5 | | V | $V_{CE}$ = −0.2 V, $I_C$ = −5.0 mA |
| Input Resistor | $R_1$ | 3.29 | 4.70 | 6.11 | kΩ | |
| Resistor Ratio | $R_1/R_2$ | 0.9 | 1.0 | 1.1 | | |
| Turn-on Time | $t_{on}$ | | | 0.5 | μs | $V_{CC}$ = −5 V, $V_{in}$ = −5 V<br>$R_L$ = 1 kΩ<br>PW = 2 μs, Duty Cycle ≦ 2 % |
| Storage Time | $t_{stg}$ | | | 3.0 | μs | |
| Turn-off Time | $t_{off}$ | | | 5.0 | μs | |

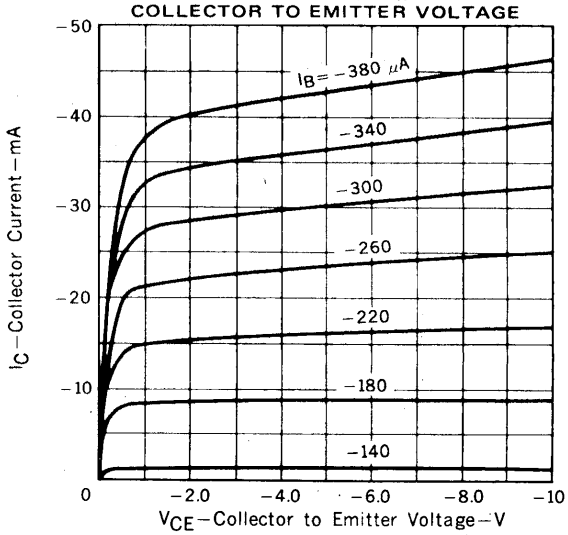
* Pulsed: PW ≦ 350 μs, Duty Cycle ≦ 2 %

## TYPICAL CHARACTERISTICS ($T_a$ = 25 °C)

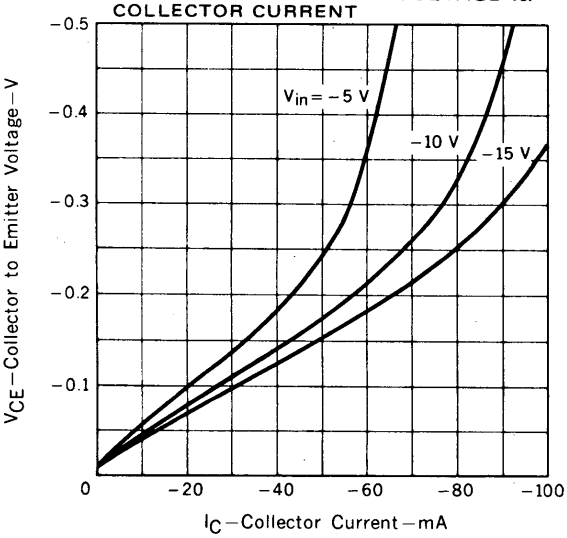
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



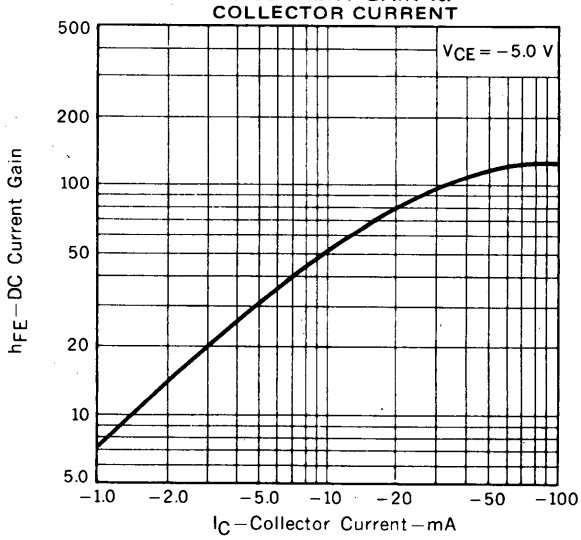

COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



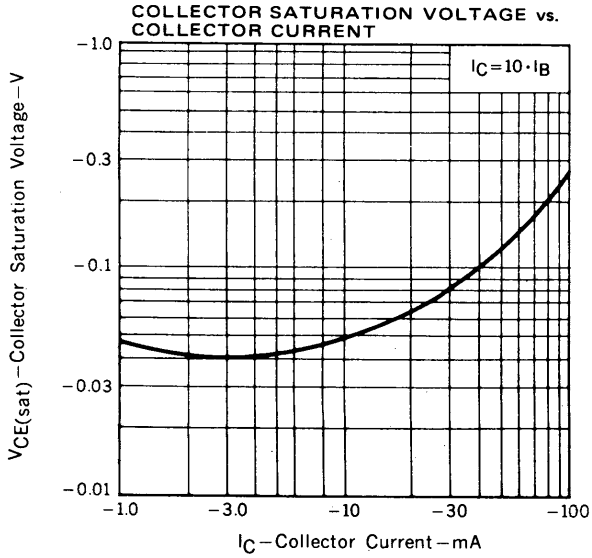

COLLECTOR TO EMITTER VOLTAGE vs. COLLECTOR CURRENT



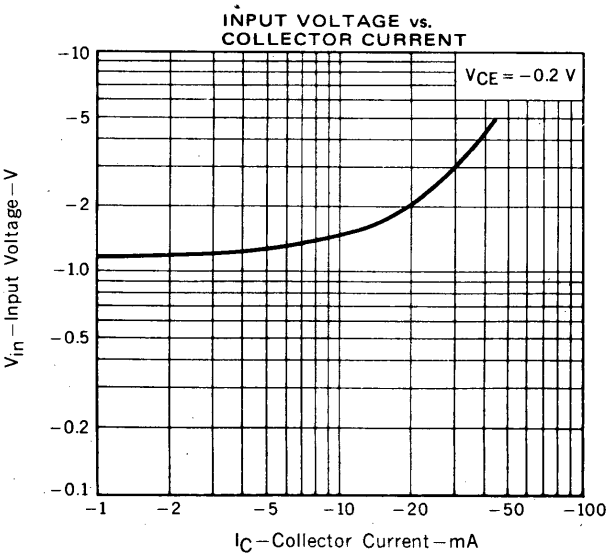

DC CURRENT GAIN vs. COLLECTOR CURRENT



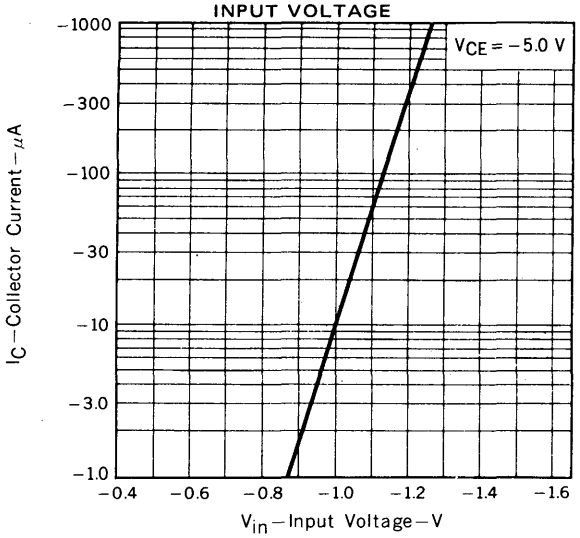

COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



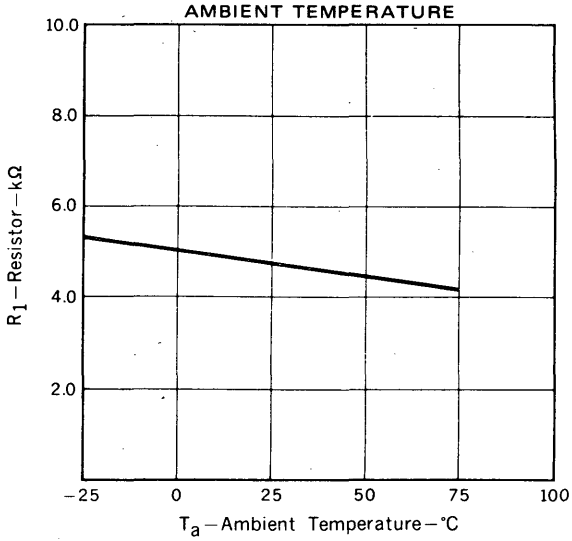

INPUT VOLTAGE vs. COLLECTOR CURRENT



COLLECTOR CURRENT vs.
INPUT VOLTAGE




RESISTOR vs.
AMBIENT TEMPERATURE



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